Wuxi Unigroup Microelectronics CO.,LTD.

30V N-Channel Trench MOSFET(Preliminary)

General Description

- Trench Power technology
- Low $R_{DS(ON)}$
- Low Gate Charge
- Optimized for fast-switching applications

Product Summary

V_{DS}	30V
I_D (at V_{GS}=10V)	85A
$R_{DS(ON)}$ (at V_{GS}=10V)	< 4.5mΩ
$R_{DS(ON)}$ (at V_{GS}=4.5V)	< 9mΩ

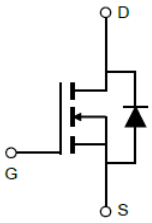
100% UIS Tested

RoHS

●Applications

- Synchronous Rectification in DC/DC and AC/DC Converters
- Isolated DC/DC Converters in Telecom and Industrial

DFN5x6



Part Number	Package Type	Form	Marking
TTG85N03AT	DFN5x6	Tape & Reel	85N03AT

Absolute Maximum Ratings (T_A =25ºC unless otherwise noted)

Parameter		Symbol	Maximum	Units
Drain-Source Voltage		V_{DS}	30	V
Gate-Source Voltage		V_{GS}	±20	V
Continuous Drain Current [B]	T_C =25ºC	I_D	51	A
	T_C =100ºC		51	
Pulsed Drain Current [A]		I_{DM}	255	A
Avalanche Current [A]		I_{AS}	30	A
Single Pulse Avalanche Energy L =0.3mH [A]		E_{AS}	135	mJ
Power Dissipation [C]	T_C =25ºC	P_D	65	W
	T_C =100ºC		32	W
Junction and Storage Temperature Range		T_J, T_{STG}	-55 to 175	ºC

Thermal Characteristics

Parameter		Symbol	Maximum	Units
Maximum Junction-to-Case	Steady-State	$R_{\theta JC}$	2.3	ºC/W
Maximum Junction-to-Ambient	Steady-State	$R_{\theta JA}$	100	

Electrical Characteristics(T_J =25ºC unless otherwise noted)

Symbol	Parameter	Conditions		Value			Units
				Min	Typ	Max	
STATIC PARAMETERS							
BV_{DSS}	Drain-Source Breakdown Voltage	I_D =250μA,V_{GS} =0V		30	--	--	V
I_{DSS}	Zero Gate Voltage Drain Current	V_{DS} =30V, V_{GS} =0V	T_J =25ºC	--	--	1	μA
			T_J =125ºC	--	--	25	
I_{GSS}	Gate-Body Leakage Current	V_{DS} =0V, V_{GS} =±20V		--	--	±100	nA
$V_{GS(th)}$	Gate Threshold Voltage	V_{DS} =V_{GS}, I_D =250μA		1	1.6	2.4	V
$R_{DS(ON)}$	Static Drain-Source On-Resistance	V_{GS} =10V, I_D =30A		--	3.6	4.5	mΩ
		V_{GS} =4.5V, I_D =30A		--	6.9	9.0	mΩ
g_{FS}	Forward Transconductance	V_{DS} =10V, I_D =20A		16	--	--	S
V_{SD}	Diode Forward Voltage	I_S =30A, V_{GS} =0V		--	--	1	V
I_S	Maximum Body-Diode Continuous Current [B]			--	--	46	A
DYNAMIC PARAMETERS							
C_{iss}	Input Capacitance	V_{GS} =0V, V_{DS} =15V, f =1MH_Z		--	2120	--	pF
C_{oss}	Output Capacitance			--	307	--	
C_{rss}	Reverse Transfer Capacitance			--	253	--	
SWITCHING PARAMETERS							
Q_g	Total Gate Charge	V_{GS} =10V,V_{DS} =15V, I_D =30A		--	40	--	nC
Q_{gs}	Gate Source Charge			--	5.4	--	
Q_{gd}	Gate Drain Charge			--	9.6	--	
$t_{D(on)}$	Turn-On Delay Time	V_{GS} =10V,V_{DS} =15V, I_D =20A, R_G =3Ω		--	15	--	ns
t_r	Turn-On Rise Time			--	32	--	
$t_{D(off)}$	Turn-Off Delay Time			--	15	--	
t_f	Turn-Off Fall Time			--	12	--	
t_{rr}	Body Diode Reverse Recovery Time	I_F =30A, di/dt =100A/μs		--	23	--	ns
Q_{rr}	Body Diode Reverse Recovery Charge			--	48	--	nC

A. Single pulse width limited by maximum junction temperature.

B. The maximum current rating is package limited.

C. The power dissipation P_D is based on $T_{J(MAX)}$ =175ºC, using junction-to-case thermal resistance, and is more useful in setting the upper dissipation limit for cases where additional heatsinking is used.

Typical Characteristics T_J = 25ºC, unless otherwise noted

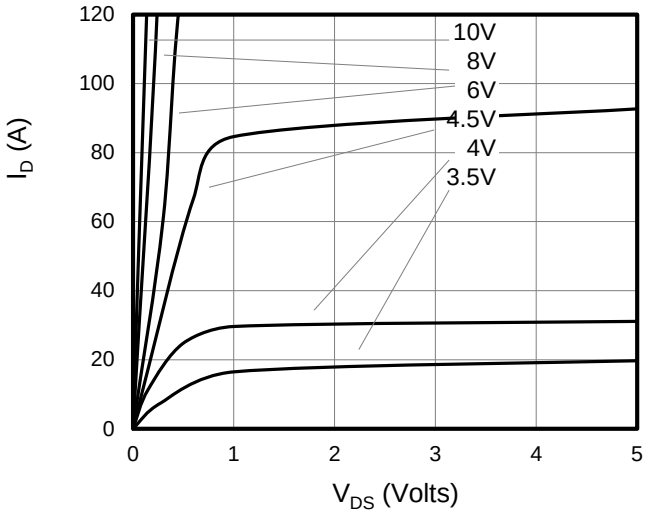


Figure 1: On-Region Characteristics

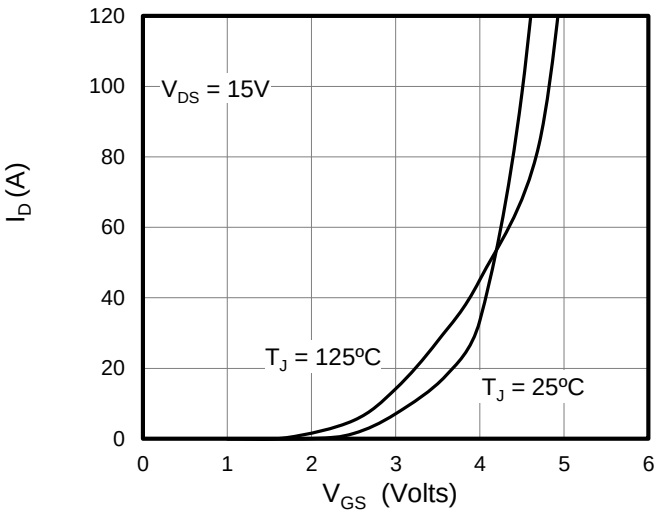


Figure 2: Transfer Characteristics

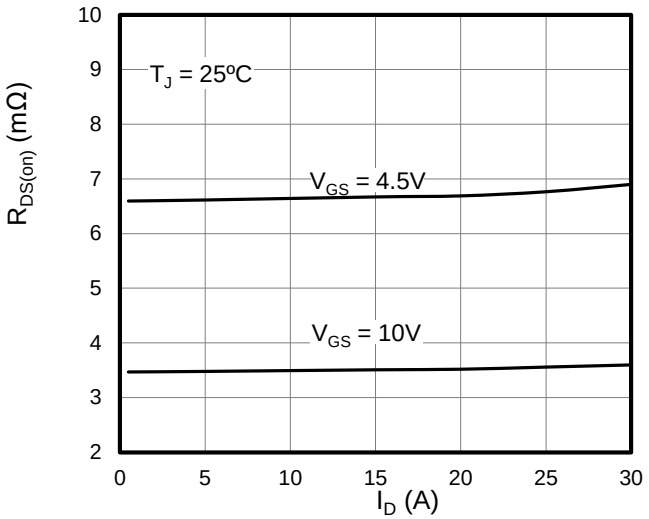


Figure 3: On-Resistance vs. Drain Current

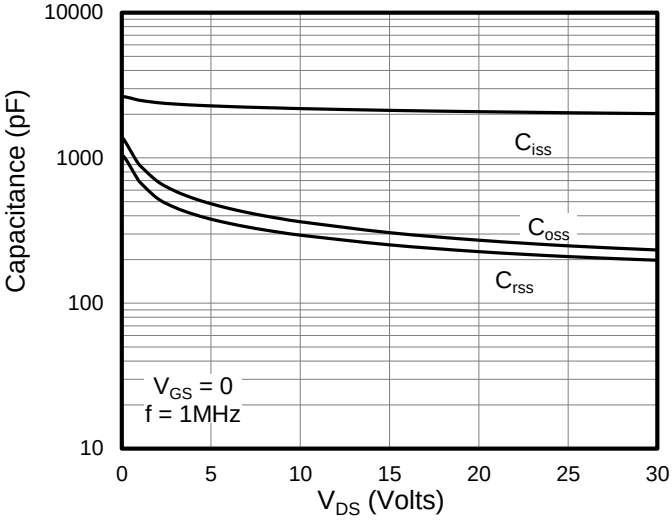


Figure 4: Capacitance Characteristics

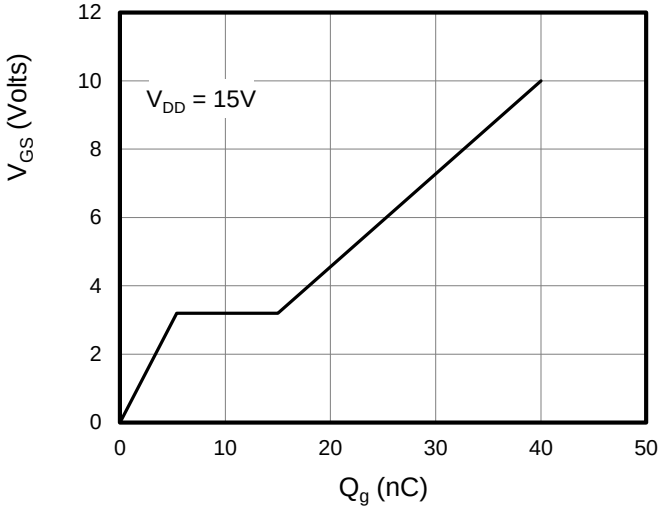


Figure 5: Gate Charge Characteristics

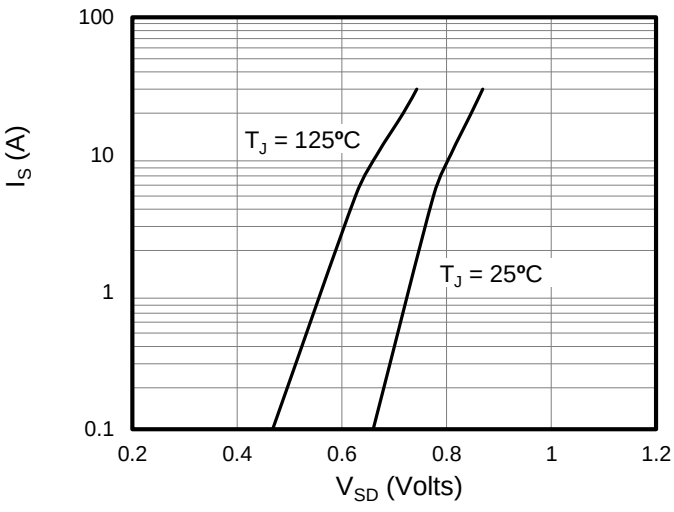


Figure 6: Body Diode Forward Voltage

Typical Characteristics T_J = 25ºC, unless otherwise noted

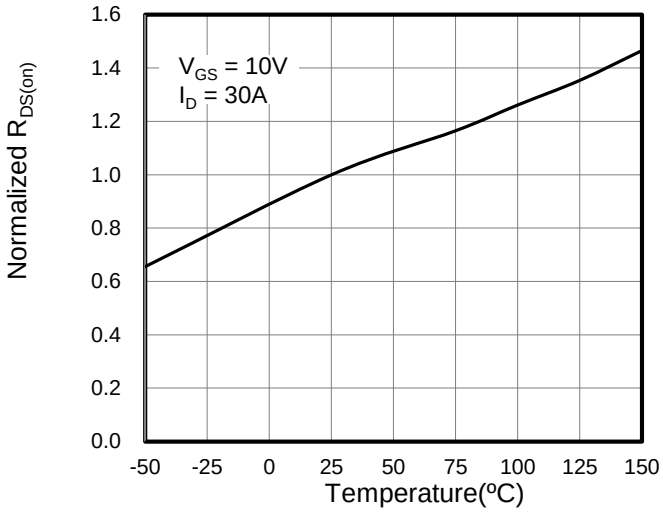


Figure 7: On-Resistance vs. Junction Temperature

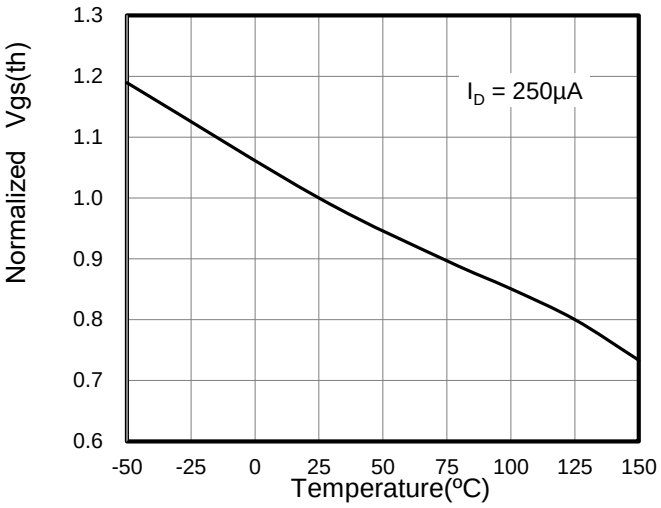


Figure 8: Vgs(th) vs. Junction Temperature

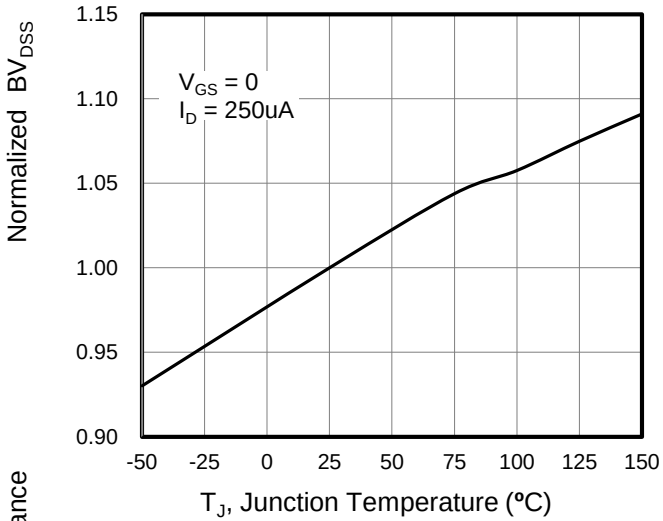


Figure 9: BV_{DSS} vs. Junction Temperature

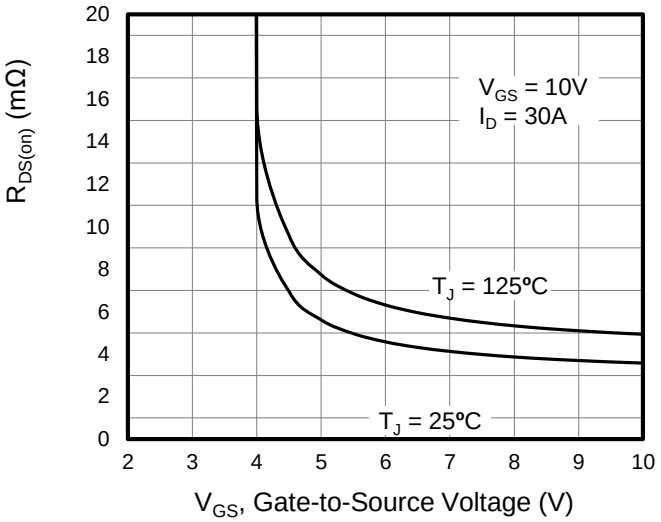


Figure 10: On-Resistance vs. Gate-Source Voltage

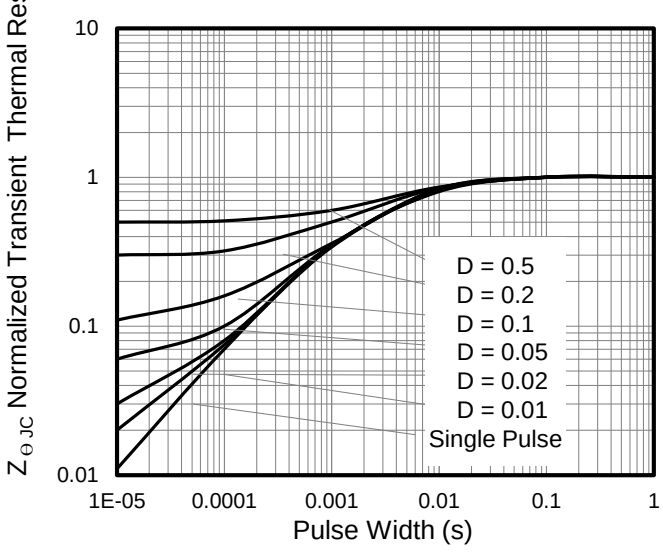


Figure 11: Normalized Transient Thermal Resistance

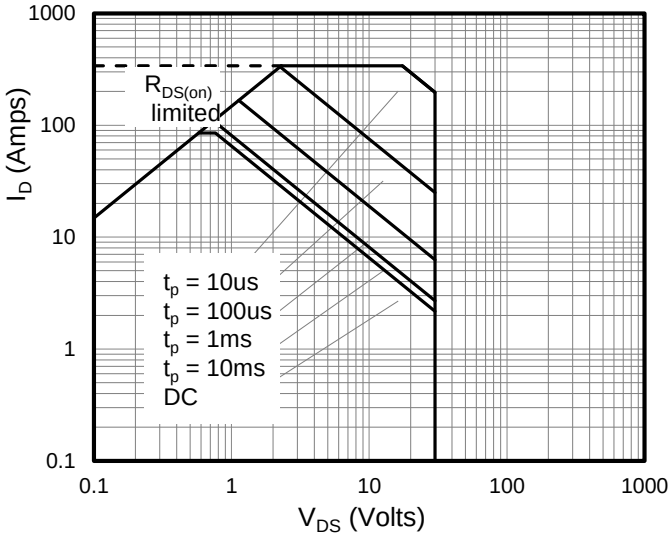


Figure 12: Safe Operating Area

Figure A：Gate Charge Test Circuit and Waveform

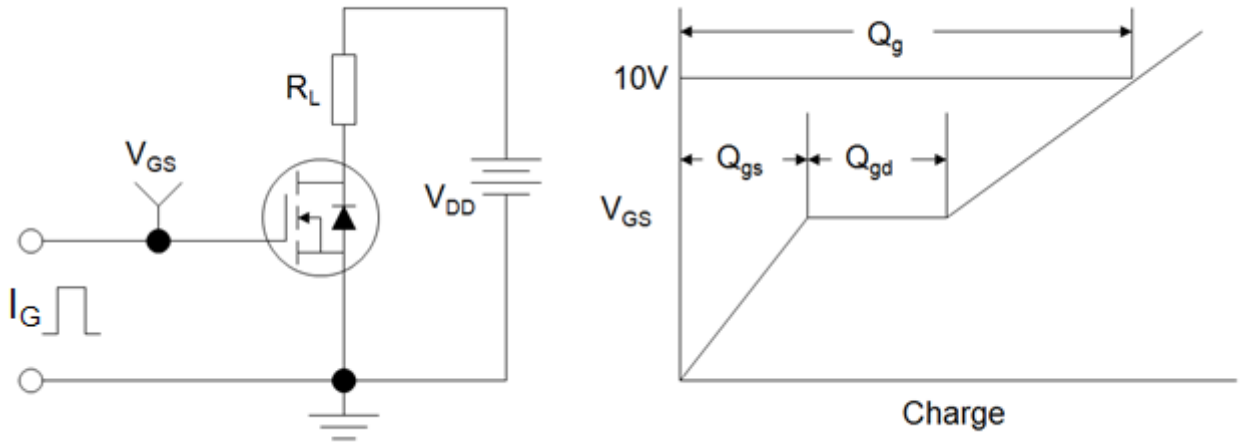


Figure B：Resistive Switching Test Circuit and Waveform

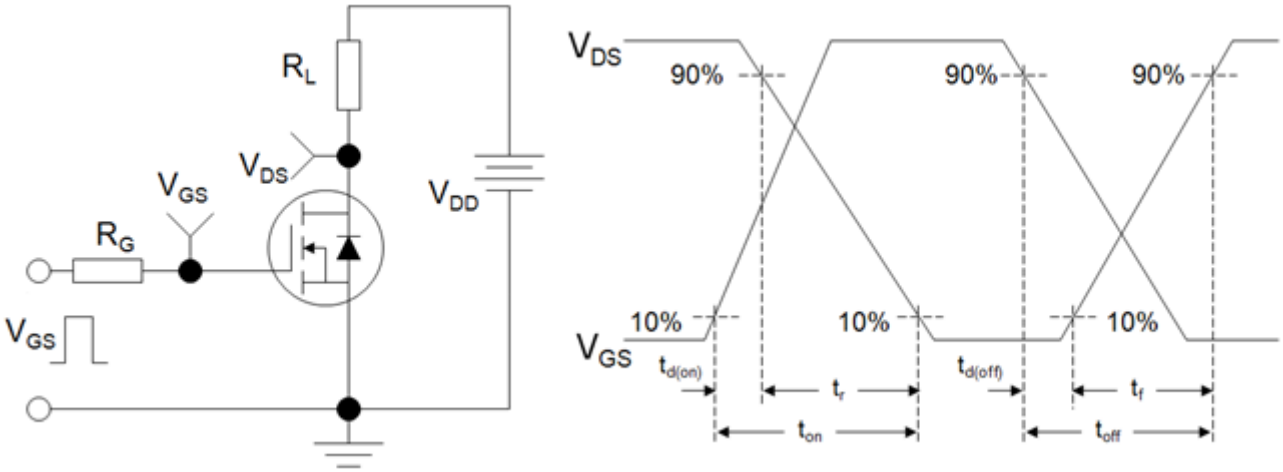
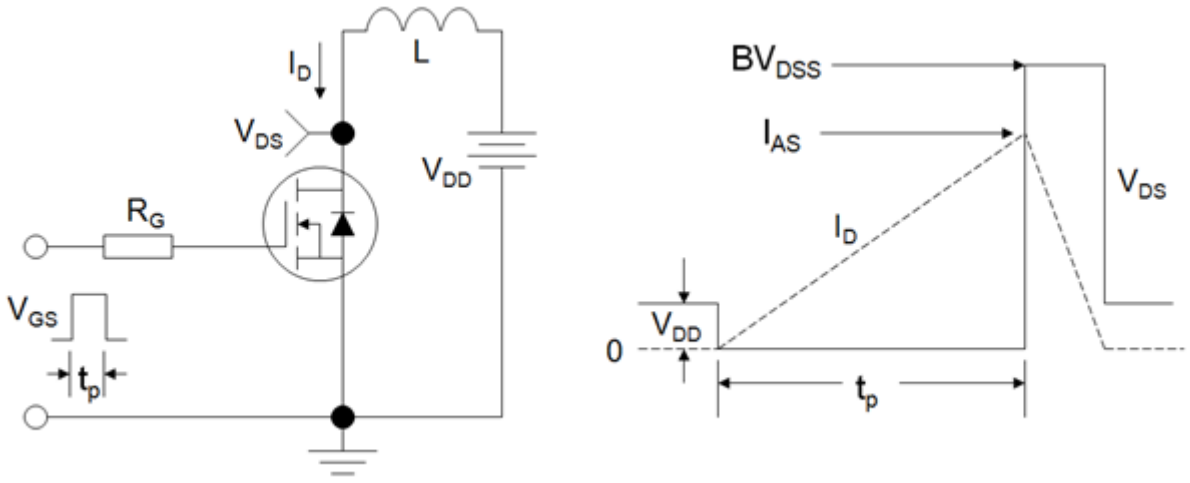
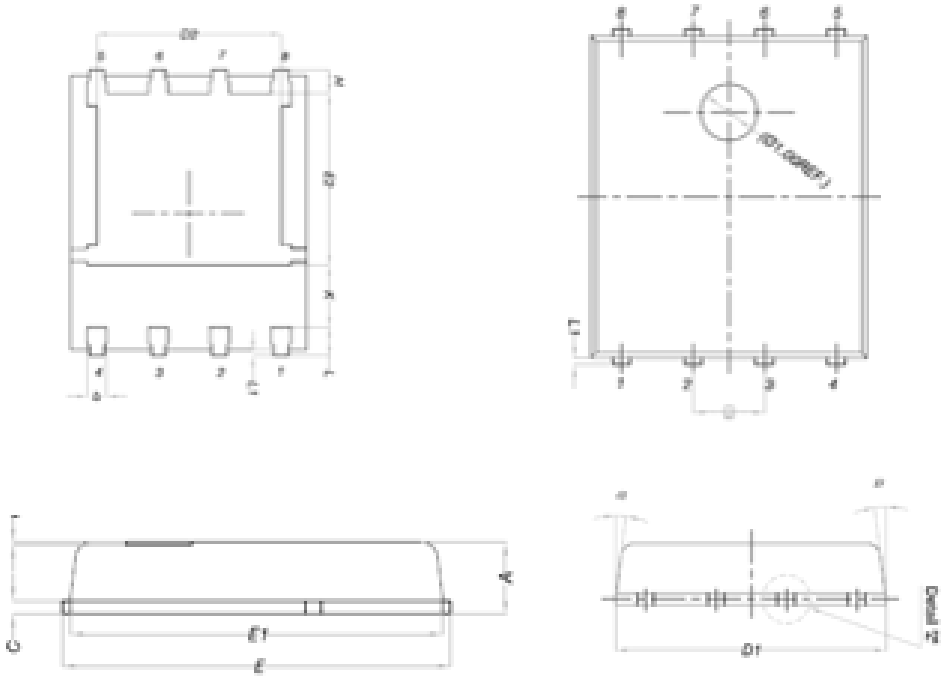


Figure C：Unclamped Inductive Switching Test Circuit and Waveform



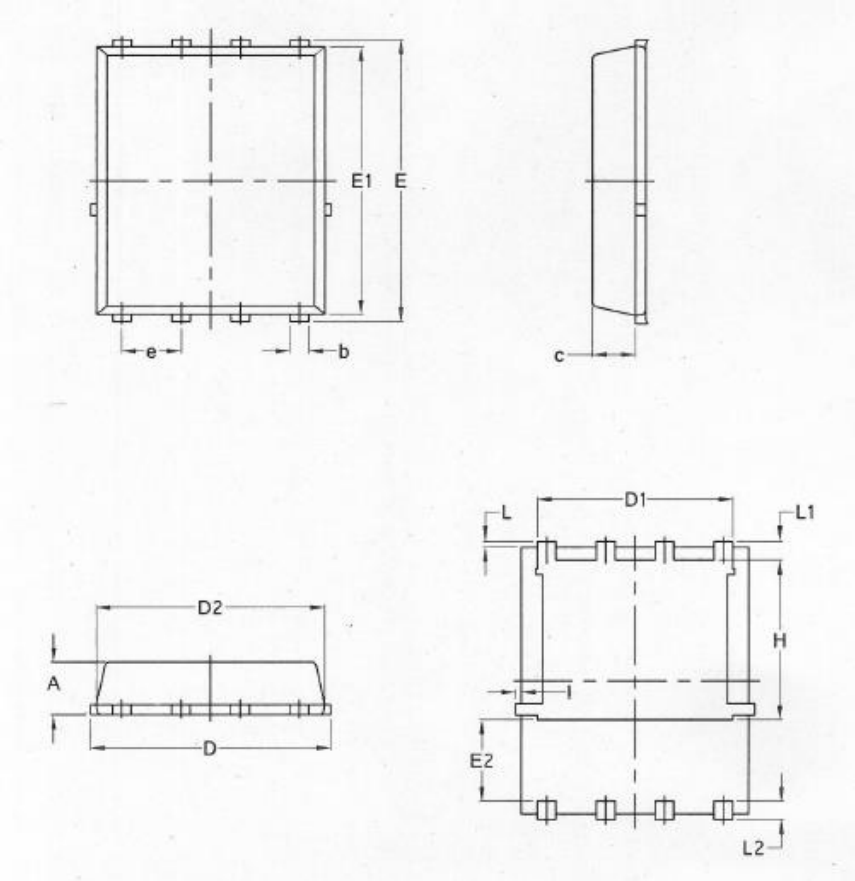
DFN5x6(M)



DIM.	MILLIMETERS		
	MIN.	NOM.	MAX.
A	0.90	1.00	1.10
A1	0	-	0.05
b	0.33	0.41	0.51
C	0.20	0.25	0.30
D1	4.80	4.90	5.00
D2	3.61	3.81	3.96

DIM.	MILLIMETERS		
	MIN.	NOM.	MAX.
E	5.90	6.00	6.10
E1	5.70	5.75	5.80
E2	3.38	3.58	3.78
e	1.27 BSC		
H	0.41	0.51	0.61
K	1.10	-	-
L	0.51	0.61	0.71
L1	0.06	0.13	0.20
α	0°	-	12°

DFN5x6(V)



	SYMBOL	COMMON			
		MM		INCH	
		MIN.	MAX.	MIN.	MAX.
	A	1.03	1.17	0.0406	0.0461
	b	0.34	0.48	0.0134	0.0189
	c	0.824	0.970	0.0324	0.0382
3	D	4.80	5.40	0.1890	0.2126
	D1	4.11	4.31	0.1618	0.1697
3	D2	4.80	5.00	0.1890	0.1969
	E	5.95	6.15	0.2343	0.2421
	E1	5.65	5.85	0.2224	0.2303
	E2	1.60	—	0.0630	—
	e	1.27 BSC		0.05 BSC	
3	L	0.05	0.25	0.0020	0.0098
	L1	0.38	0.50	0.0150	0.0197
	L2	0.38	0.50	0.0150	0.0197
4	H	3.30	3.50	0.1299	0.1378
	I	—	0.18	—	0.0070

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